

SCDS188 - JANUARY 2005

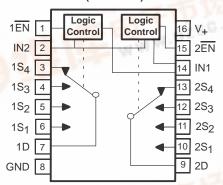
#### **Description**

The TS3A5017 is a dual single-pole quadruple-throw (4:1) analog switch that is designed to operate from 2.3 V to 3.6 V. This device can handle both digital and analog signals, and signals up to  $V_{+}$  can be transmitted in either direction.

#### **Applications**

- Sample-and-Hold Circuit
- Battery-Powered Equipment
- Audio and Video Signal Routing
- Communication Circuits

SOIC, SSOP, TSSOP, OR TVSOP PACKAGE (TOP VIEW)



#### **FUNCTION TABLE**

EN	IN2	IN1	D TO S S TO D
192 5	L	L	D = S <sub>1</sub>
L	L	Н	D = S <sub>2</sub>
L	Н	L	D = S <sub>3</sub>
L	Н	Н	D = S <sub>4</sub>
Н	X	X	OFF

#### **Features**

- Isolation in the Powered-Down Mode, V<sub>+</sub> = 0
- Low ON-State Resistance (10 Ω)
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 2.3-V to 3.6-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
  - 2000-V Human-Body Model (A114-B, Class II)
  - 1000-V Charged-Device Model (C101)

#### Summary of Characteristics

 $V_{+} = 3.3 \text{ V}, T_{A} = 25^{\circ}\text{C}$ 

Configuration	Dual Analog MUX/DEMUX (4:1 MUX/DEMUX)
Number of channels	2
ON-state resistance (ron)	11 Ω
ON-state resistance match (Δron)	1Ω
ON-state resistance flatness (ron(flat))	7Ω
Turn-on/turn-off time (tON/tOFF)	5 ns/1.5 ns
Charge injection (Q <sub>C</sub> )	5 pC
Bandwidth (BW)	165 MHz
OFF isolation (OISO)	-48 dB at 10 MHz
Crosstalk (XTALK)	-49 dB at 10 MHz
Total harmonic distortion (THD)	0.21%
Leakage current (ID(OFF)/IS(OFF))	±0.1 μA
Power-supply current (I <sub>+</sub> )	2.5 μΑ
Package option	16-pin SOIC, SSOP, TSSOP, or TVSOP

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



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#### **ORDERING INFORMATION**

TA	PACKAGE(1)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
	QFN – RGY Tape and reel TS3A5017RGYR		TS3A5017RGYR	YA017
	SOIC - D	Tube	TS3A5017D	TS3A5017
	2010 - D	Tape and reel	TS3A5017DR	153A5017
-40°C to 85°C	SSOP (QSOP) – DBQ	Tape and reel	TS3A5017DBQR	YA017
	TSSOP – PW	Tube	TS3A5017PW	YA017
	1330F - FVV	Tape and reel	TS3A5017PWR	TAUT
	TVSOP - DGV	Tape and reel	TS3A5017DGVR	YA017

<sup>(1)</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

## Absolute Minimum and Maximum Ratings(1)(2)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V <sub>+</sub>	Supply voltage range(3)		-0.5	4.6	V
$V_S, V_D$	Analog voltage range(3)(4)		-0.5	4.6	V
ΙK	Analog port diode current	V <sub>S</sub> , V <sub>D</sub> < 0	-50		mA
IS, ID	On-state switch current	V <sub>S</sub> , V <sub>D</sub> = 0 to 7 V	-128	128	mA
VI	Digital input voltage range(3)(4)		-0.5	4.6	V
ΙΚ	Digital input clamp current	V <sub>I</sub> < 0	-50		mA
I <sub>+</sub>	Continuous current through V <sub>+</sub>			100	mA
I <sub>GND</sub>	Continuous current through GND		-100		mA
		D package		73	
	<b>5</b> (5)	DB package		82	
$\theta$ JA	Package thermal impedance <sup>(5)</sup>	DGV package		120	°C/W
		DW package		108	
T <sub>stg</sub>	Storage temperature range		-65	150	°C

<sup>(1)</sup> Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) The package thermal impedance is calculated in accordance with JESD 51-7.



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# Electrical Characteristics for 3.3-V Supply<sup>(1)</sup> $V_+ = 3 \text{ V to } 3.6 \text{ V}, T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CONDITIONS			٧+	MIN	TYP	MAX	UNIT
Analog Switch						-			
Analog signal range	V <sub>D</sub> , V <sub>S</sub>					0		٧+	٧
ON-state resistance	r <sub>on</sub>	$0 \le V_S \le V_+,$ $I_D = -32 \text{ mA},$	Switch ON, See Figure 13	25°C Full	3 V		11	12 14	Ω
ON-state resistance match	Δr <sub>on</sub>	V <sub>S</sub> = 2.1 V,	Switch ON,	25°C	3 V		1	2	Ω
between channels		$I_D = -32 \text{ mA},$	See Figure 13	Full				3	
ON-state resistance	ron(flat)	$0 \le V_S \le V_+$	Switch ON,	25°C	3 V		7	9	Ω
flatness	ion(liat)	$I_D = -32 \text{ mA},$	See Figure 13	Full	0 1			10	4
	lo(OFF)	$V_S = 1 \text{ V}, V_D = 3 \text{ V},$	Switch OFF,	25°C	3.6 V	-0.1	0.05	5 0.1	
S OFF leakage	IS(OFF)	$V_S = 3 \text{ V}, V_D = 1 \text{ V},$	See Figure 14	Full	5.0 V	-0.2		0.2	μA
current	long a process	$V_S = 0 \text{ to } 3.6 \text{ V},$	Switch OFF,	25°C	0 V	-1	0.5	1	,
	ISPWR(OFF)	$V_D = 3.6 \text{ V to 0},$	See Figure 14	Full		-5		5	
	In (OFF)	$V_D = 1 \text{ V}, V_S = 3 \text{ V},$	Switch OFF,	25°C	3.6 V	-0.1	0.05	0.1	
D OFF leakage	ID(OFF)	$V_D = 3 \text{ V}, V_S = 3 \text{ V},$	See Figure 14	Full	3.0 V	-0.2		0.2	μΑ
current	IDDA DOCTO	$V_D = 0 \text{ to } 3.6 \text{ V},$	Switch OFF,	25°C	0 V	-1	0.5	1	<b>,</b>
	IDPWR(OFF)	$V_S = 3.6 \text{ V to } 0,$	See Figure 14	Full	0 0	-5		5	
S ON leakage	locon	$V_S = 1 V, V_D = Open,$	Switch ON,	25°C	3.6 V	-0.1	0.05	0.1	μΑ
current	IS(ON)	$V_S = 3 V$ , $V_D = Open$ ,	See Figure 15	Full	5.0 V	-0.2		0.2	μΛ
D ON leakage	la cas n	$V_D = 1 V$ , $V_S = Open$ ,	Switch ON,	25°C	261/	-0.1	0.05	0.1	^
current	ID(ON)	$V_D = 3 V$ , $V_S = Open$ ,	See Figure 15	Full	3.6 V	-0.2		0.2	μΑ
Digital Control Inp	outs (IN1, IN2	, EN)(2)							
Input logic high	VIH			Full		2	•	5.5	V
Input logic low	V <sub>IL</sub>			Full		0		8.0	V
Input leakage	կн, կլ	V <sub>I</sub> = 5.5 V or 0		25°C	3.6 V	-1	0.05	1	μА
current	1117 12	'	Full		-1		1	μΛ	

<sup>(1)</sup> The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

<sup>(2)</sup> All unused digital inputs of the device must be held at V+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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# Electrical Characteristics for 3.3-V Supply<sup>(1)</sup> (continued) $V_+ = 3 \text{ V to } 3.6 \text{ V}, T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		TA	٧+	MIN	TYP	MAX	UNIT
Dynamic					•				
Turn-on time	4	V <sub>D</sub> = 2 V,	C <sub>L</sub> = 35 pF,	25°C	3.3 V	1	5	9.5	20
rum-on ume	tON	$R_L = 300 \Omega$ ,	See Figure 17	Full	3 V to 3.6 V	1		10.5	ns
Turn-off time	torr	$V_D = 2 V$ ,	$C_L = 35 pF$ ,	25°C	3.3 V	0.5	1.5	3.5	ns
Tarr on anio	tOFF	$R_L = 300 \Omega$ ,	See Figure 17	Full	3 V to 3.6 V	0.5		4.5	110
Charge injection	QC	V <sub>GEN</sub> = 0, R <sub>GEN</sub> = 0 C <sub>L</sub> = 0.1 nF,	See Figure 22	25°C	3.3 V		5		рС
S OFF capacitance	C <sub>S(OFF)</sub>	V <sub>S</sub> = V <sub>+</sub> or GND, Switch OFF,	See Figure 16	25°C	3.3 V		19		pF
D OFF capacitance	C <sub>D(OFF)</sub>	V <sub>D</sub> = V <sub>+</sub> or GND, Switch OFF,	See Figure 16	25°C	3.3 V		4.5		pF
S ON capacitance	C <sub>S(ON)</sub>	V <sub>S</sub> = V <sub>+</sub> or GND, Switch ON,	See Figure 16	25°C	3.3 V		25		pF
D ON capacitance	C <sub>D(ON)</sub>	V <sub>D</sub> = V <sub>+</sub> or GND, Switch ON,	See Figure 16	25°C	3.3 V		25		pF
Digital input capacitance	CI	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	3.3 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$ , Switch ON,	See Figure 18	25°C	3.3 V		165		MHz
OFF isolation	O <sub>ISO</sub>	$R_L = 50 \Omega$ , f = 10 MHz,	Switch OFF, See Figure 19	25°C	3.3 V		-48		dB
Crosstalk	XTALK	$R_L = 50 \Omega$ , $f = 10 MHz$ ,	Switch ON, See Figure 20	25°C	3.3 V		-49		dB
Crosstalk Adjacent	XTALK(ADJ)	$R_L = 50 \Omega$ , f = 10 MHz,	Switch ON, See Figure 21	25°C	3.3 V		-74		dB
Total harmonic distortion	THD	$R_L = 600 \Omega$ , $C_L = 50 pF$ ,	f = 20 Hz to 20 kHz, See Figure 23	25°C	3.3 V		0.21		%
Supply	•	•		•	•				
Positive supply current	I <sub>+</sub>	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	3.6 V		2.5	7	μΑ

<sup>(1)</sup> The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum



# TS3A5017 $14\text{-}\Omega \text{ DUAL SP4T ANALOG SWITCH} \\ 3.3\text{-}V/2.5\text{-}V \text{ DUAL 4:1 ANALOG MULTIPLEXER/DEMULTIPLEXER}$

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### Electrical Characteristics for 2.5-V Supply<sup>(1)</sup>

 $V_{+} = 2.3 \text{ V to } 2.7 \text{ V, } T_{\text{A}} = -40^{\circ}\text{C} \text{ to } 85^{\circ}\text{C} \text{ (unless otherwise noted)}$ 

PARAMETER	SYMBOL	TEST CONDIT	TIONS	TA	٧+	MIN	TYP	MAX	UNIT	
Analog Switch									·	
Analog signal range	V <sub>D</sub> , V <sub>S</sub>					0		٧+	V	
ON-state	r	$0 \le V_S \le V_+$	Switch ON,	25°C	2.3 V		20.5	22	Ω	
resistance	r <sub>on</sub>	$I_D = -24 \text{ mA},$	See Figure 13	Full	2.5 V			24	52	
ON-state resistance match	Δr <sub>on</sub>	VS = 1.6 V,	Switch ON,	25°C	2.3 V		1	2	Ω	
between channels	2.011	$I_D = -24 \text{ mA},$	See Figure 13	Full	2.0 V			3	32	
ON-state		$0 \le V_S \le V_+$	Switch ON,	25°C	0.01/		16	18		
resistance flatness	ron(flat)	$I_D = -24 \text{ mA},$	See Figure 13	Full	2.3 V			20	Ω	
	1	$V_S = 0.5 \text{ V}, V_D = 2.2 \text{ V},$	Switch OFF,	25°C	2.7 V	-0.1	0.05	0.1	0.1	
S OFF leakage	I <sub>S(OFF)</sub>	$V_S = 2.2 \text{ V}, V_D = 0.5 \text{ V},$	See Figure 14	Full	2.7 V	-0.2		0.2	μΑ	
current		$V_S = 0 \text{ to } 3.6 \text{ V},$	Switch OFF,	25°C	0.1/	-1	0.5	1		
	ISPWR(OFF)	$V_D = 3.6 \text{ V to } 0,$	See Figure 14	Full	0 V	-5		5		
	1	$V_D = 0.5 \text{ V}, V_S = 2.2 \text{ V},$	Switch OFF,	25°C	2.7 V	-0.1	0.05	0.1		
D OFF leakage	ID(OFF)	$V_D = 2.2 \text{ V}, V_S = 0.5 \text{ V},$	See Figure 14	Full	2.7 V	-0.2		0.2	μΑ	
current	<b>.</b>	$V_D = 0 \text{ to } 5.5 \text{ V},$	Switch OFF,	25°C	0 V	-1	0.5	1	μ	
	IDPWR(OFF)	$V_S = 5.5 \text{ V to } 0,$	See Figure 14	Full	0 0	-5		5		
S ON leakage	1	$V_S = 0.5 \text{ V}, V_D = \text{Open},$	Switch ON,	25°C	2.7 V	-0.1	0.05	0.1	^	
current	IS(ON)	$V_S = 2.2 \text{ V}, V_D = \text{Open},$	See Figure 15	Full	2.7 V	-0.2		0.2	μA	
D ON Joshova		V <sub>D</sub> = 0.5 V, V <sub>S</sub> = Open,	Switch ON,	25°C	0.71/	-0.1	0.05	0.1		
ON leakage current	I <sub>D</sub> (ON)	or $V_D = 2.2 \text{ V}, V_S = \text{Open},$	See Figure 15	Full	2.7 V	-0.2		0.2	μΑ	
Digital Control Inp	outs (IN1, IN2	)(2)		_						
Input logic high	VIH			Full		1.7		5.5	V	
Input logic low	V <sub>IL</sub>			Full		0		0.7	V	
Input leakage	կн, կլ	V <sub>I</sub> = 5.5 V or 0		25°C	2.7 V	-1	0.05	1	μΑ	
current IIH, IIL VI = 3.3 V or 0		Full		-1		1	μΛ			

<sup>(1)</sup> The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

<sup>(2)</sup> All unused digital inputs of the device must be held at V<sub>+</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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# Electrical Characteristics for 2.5-V Supply<sup>(1)</sup> (continued) $V_+ = 2.3 \text{ V}$ to 2.7 V, $T_A = -40 ^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST COM	NDITIONS	TA	٧+	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	4	V <sub>D</sub> = 1.5 V,	C <sub>L</sub> = 35 pF,	25°C	2.5 V	1.5	5	8	
rum-on time	tON	$R_L = 300 \Omega$	See Figure 17	Full	2.3 V to 2.7 V	1		10	ns
Turn-off time	4	V <sub>D</sub> = 1.5 V,	C <sub>L</sub> = 35 pF,	25°C	2.5 V	0.3	2	4.5	
rum-on ume	<sup>t</sup> OFF	$R_L = 300 \Omega$ ,	See Figure 17	Full	2.3 V to 2.7 V	0.3		6	ns
Charge injection	QC	V <sub>GEN</sub> = 0, R <sub>GEN</sub> = 0 C <sub>L</sub> = 0.1 nF,	See Figure 22	25°C	2.5 V				рС
S OFF capacitance	C <sub>S(OFF)</sub>	V <sub>S</sub> = V <sub>+</sub> or GND, Switch OFF,	See Figure 16	25°C	2.5 V		18.5		pF
D OFF capacitance	C <sub>D(OFF)</sub>	V <sub>D</sub> = V <sub>+</sub> or GND, Switch OFF,	See Figure 16	25°C	2.5 V		45		pF
S ON capacitance	C <sub>NC(ON)</sub>	$V_S = V_+ \text{ or GND},$ Switch ON,	See Figure 16	25°C	2.5 V		24		pF
D ON capacitance	C <sub>D(ON)</sub>	V <sub>D</sub> = V <sub>+</sub> or GND, Switch ON,	See Figure 16	25°C	2.5 V		24		pF
Digital input capacitance	Cl	$V_I = V_+$ or GND,	See Figure 16	25°C	2.5 V		2		pF
Bandwidth	BW	$R_L = 50 \Omega$ , Switch ON,	See Figure 18	25°C	2.5 V		165		MHz
OFF isolation	O <sub>ISO</sub>	$R_L = 50 \Omega$ , $f = 10 MHz$ ,	Switch OFF, See Figure 19	25°C	2.5 V		-48		dB
Crosstalk	XTALK	$R_L = 50 \Omega$ , f = 10 MHz,	Switch ON, See Figure 20	25°C	2.5 V		-49		dB
Crosstalk Adjacent	XTALK(ADJ)	$R_L = 50 \Omega,$ f = 10 MHz,	Switch ON, See Figure 21	25°C	3.3 V		-74		dB
Total harmonic distortion	THD	$R_L = 600 \Omega$ , $C_L = 50 pF$ ,	f = 20 Hz to 20 kHz, See Figure 23	25°C	2.5 V		0.29		%
Supply		•							
Positive supply current	1+	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	25°C Full	2.7 V		2.5	7	μΑ

<sup>(1)</sup> The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

#### TYPICAL PERFORMANCE

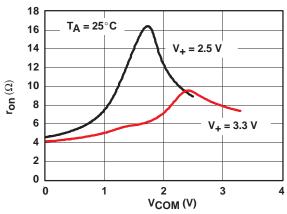


Figure 1. ron vs V<sub>COM</sub>

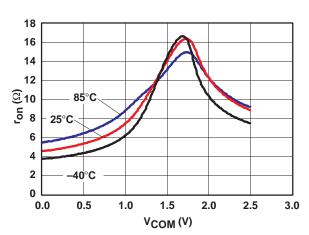


Figure 3.  $r_{on}$  vs  $V_{COM}$  ( $V_{+} = 5$  V)

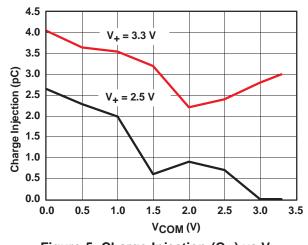
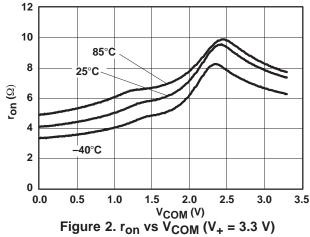


Figure 5. Charge-Injection (Q<sub>C</sub>) vs V<sub>COM</sub>



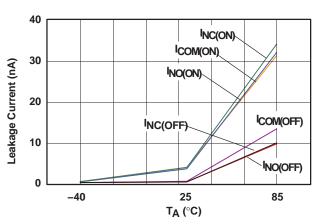


Figure 4. Leakage Current vs Temperature  $(V_+ = 5.5 \text{ V})$ 

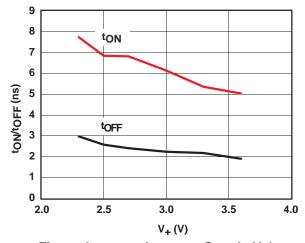
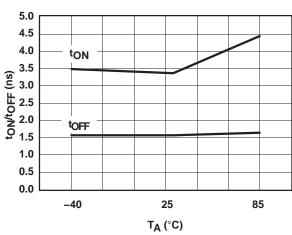


Figure 6. t<sub>ON</sub> and t<sub>OFF</sub> vs Supply Voltage



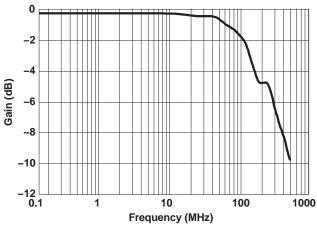
#### TYPICAL PERFORMANCE



2.0 1.8 Logic Level Threshold (nA) 1.6 ٧<sub>IH</sub> 1.4 1.2  $V_{IL}$ 1.0 8.0 0.6 0.4 0.2 0.0 3.6 2.0 2.2 2.6 2.8 3.0 3.2 3.4 V<sub>+</sub> (V)

Figure 7.  $t_{ON}$  and  $t_{OFF}$  vs Temperature (V<sub>+</sub> = 5 V)

Figure 8. Logic-Level Threshold vs V<sub>+</sub>



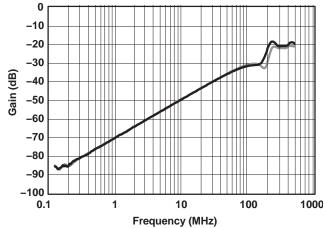
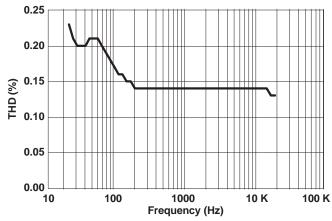


Figure 9. Bandwidth (Gain vs Frequency)  $(V_+ = 5 V)$ 

Figure 10. OFF Isolation and Crosstalk vs Frequency (V<sub>+</sub> = 5 V)



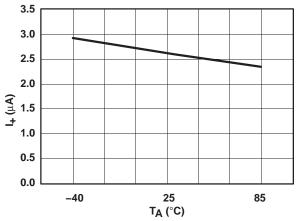


Figure 11. Total Harmonic Distortion vs Frequency

Figure 12. Power-Supply Current vs Temperature (V<sub>+</sub> = 3.6 V)



# TS3A5017 ${\it 14-}\Omega \ {\it DUAL\ SP4T\ ANALOG\ SWITCH}$ 3.3-V/2.5-V DUAL 4:1 ANALOG MULTIPLEXER/DEMULTIPLEXER

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#### **PIN DESCRIPTION**

PIN NUMBER	NAME	DESCRIPTION	
1	1EN	Enable (active low)	
2	IN2	Digital control pin to connect D to S	
3	1S <sub>4</sub>	Analog I/O	
4	1S <sub>3</sub>	Analog I/O	
5	1S <sub>2</sub>	Analog I/O	
6	1S <sub>1</sub>	Analog I/O	
7	1D	Common	
8	GND	Ground	
9	2D	Common	
10	2S <sub>1</sub>	Analog I/O	
11	2S <sub>2</sub>	Analog /O	
12	2S <sub>3</sub>	Analog I/O	
13	2S <sub>4</sub>	Analog I/O	
14	IN1	Digital control pin to connect D to S	
15	2EN	Enable (active low)	
16	٧+	Power supply	



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#### PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
VD	Voltage at D
٧s	Voltage at S
r <sub>on</sub>	Resistance between D and S ports when the channel is ON
$\Delta r_{on}$	Difference of ron between channels in a specific device
ron(flat)	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
IS(OFF)	Leakage current measured at the S port, with the corresponding channel (S to D) in the OFF state
ISPWR(OFF)	Leakage current measured at the S port, under powered down mode, V <sub>+</sub> = 0
IS(ON)	Leakage current measured at the S port, with the corresponding channel (S to D) in the ON state and the output (D) open
I <sub>D</sub> (OFF)	Leakage current measured at the D port, with the corresponding channel (D to S) in the OFF state
IDPWR(OFF)	Leakage current measured at the D port, under powered down mode, V <sub>+</sub> = 0
I <sub>D</sub> (ON)	Leakage current measured at the D port, with the corresponding channel (D to S) in the ON state and the output (S) open
VIH	Minimum input voltage for logic high for the control input (IN, EN)
V <sub>IL</sub>	Maximum input voltage for logic low for the control input (IN, EN)
VI	Voltage at the control input (IN, EN)
I <sub>IH</sub> , I <sub>IL</sub>	Leakage current measured at the control input (IN, EN)
tON	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (D or S) signal when the switch is turning ON.
tOFF	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (D or S) signal when the switch is turning OFF.
QC	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (S or D) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_D$ , $C_L$ is the load capacitance, and $\Delta V_D$ is the change in analog output voltage.
C <sub>S(OFF)</sub>	Capacitance at the S port when the corresponding channel (S to D) is OFF
C <sub>S(ON)</sub>	Capacitance at the S port when the corresponding channel (S to D) is ON
C <sub>D(OFF)</sub>	Capacitance at the D port when the corresponding channel (D to S) is OFF
C <sub>D(ON)</sub>	Capacitance at the D port when the corresponding channel (D to S) is ON
Cl	Capacitance of control input (IN)
O <sub>ISO</sub>	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (S to D) in the OFF state.
X <sub>TALK</sub>	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an adjacent ON channel ( $1S_1$ to $2S_1$ ). This is measured in a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.
I <sub>+</sub>	Static power-supply current with the control (IN) pin at V <sub>+</sub> or GND

#### PARAMETER MEASUREMENT INFORMATION

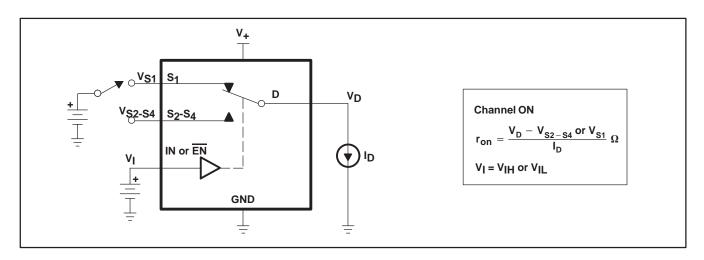


Figure 13. ON-State Resistance (ron)

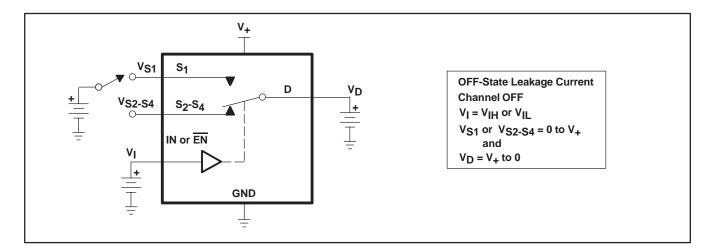


Figure 14. OFF-State Leakage Current (I<sub>D(OFF)</sub>, I<sub>S(OFF)</sub>, I<sub>NO(OFF)</sub>

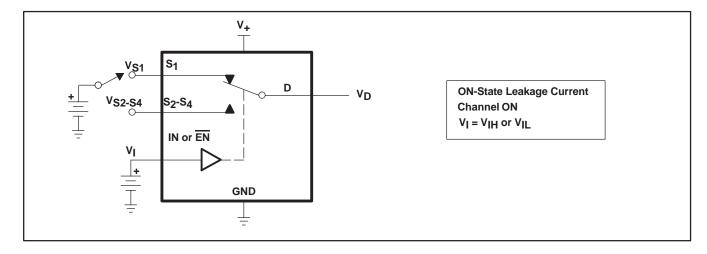


Figure 15. ON-State Leakage Current (I<sub>D(ON)</sub>, I<sub>S(ON)</sub>)



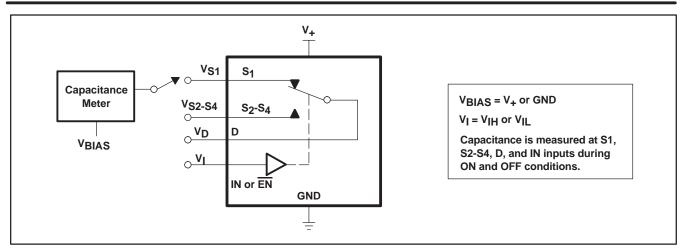
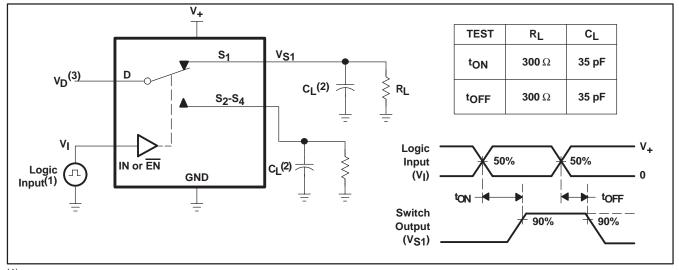


Figure 16. Capacitance ( $C_I$ ,  $C_{D(OFF)}$ ,  $C_{D(ON)}$ ,  $C_{S(OFF)}$ ,  $C_{S(ON)}$ )



- (1) All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_Q = 50 \Omega$ ,  $t_f < 5$  ns,  $t_f < 5$  ns.
- (2) C<sub>1</sub> includes probe and jig capacitance.
- (3) See Electrical Characteristics for V<sub>D</sub>.

Figure 17. Turn-On (t<sub>ON</sub>) and Turn-Off Time (t<sub>OFF</sub>)

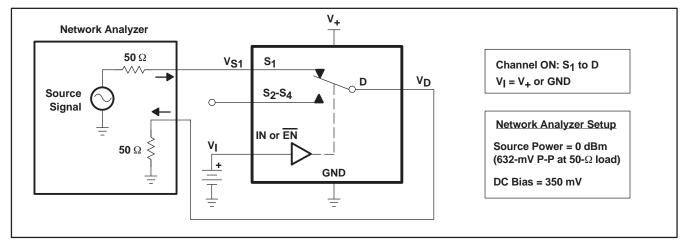


Figure 18. Bandwidth (BW)



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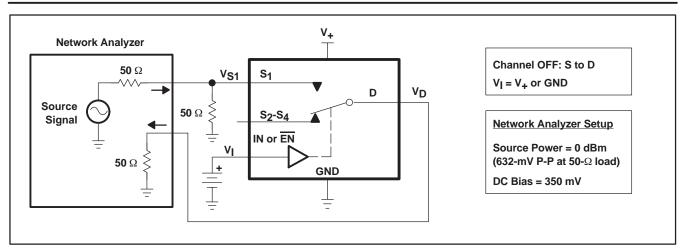


Figure 19. OFF Isolation (O<sub>ISO</sub>)

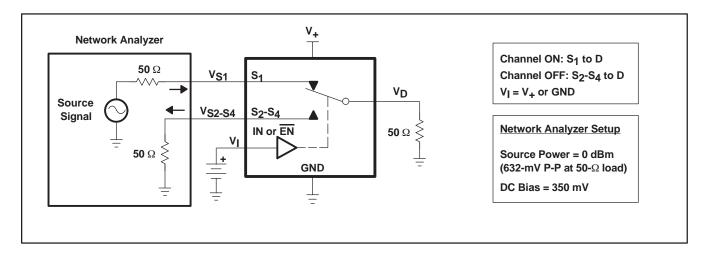


Figure 20. Crosstalk (X<sub>TALK</sub>)

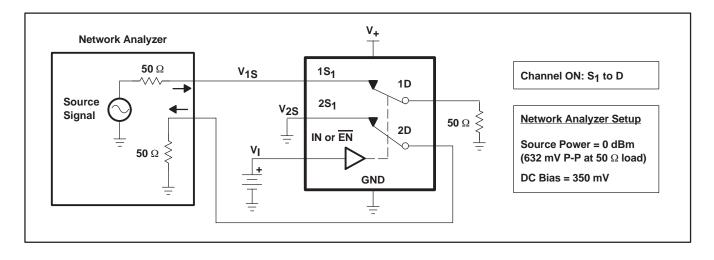
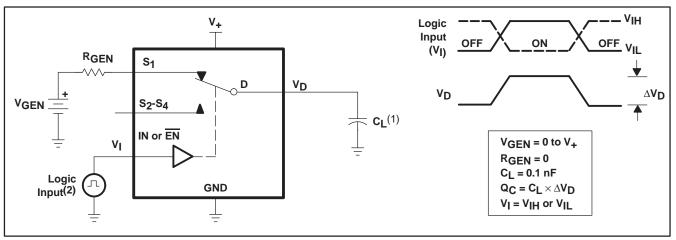


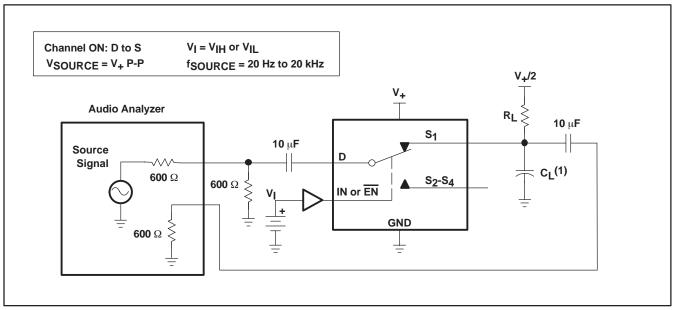
Figure 21. Adjacent Crosstalk





- (1) C<sub>L</sub> includes probe and jig capacitance.
- (2) All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50 \Omega$ ,  $t_f < 5 \text{ ns}$ .

Figure 22. Charge Injection (Q<sub>C</sub>)



(1) C<sub>L</sub> includes probe and jig capacitance.

Figure 23. Total Harmonic Distortion (THD)





30-Aug-2005

#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan <sup>(2)</sup>	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
TS3A5017D	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017DBQR	ACTIVE	SSOP/ QSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
TS3A5017DBQRE4	ACTIVE	SSOP/ QSOP	DBQ	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1YEAR
TS3A5017DE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017DGVR	ACTIVE	TVSOP	DGV	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017DGVRE4	ACTIVE	TVSOP	DGV	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017DR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017DRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017PW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017PWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017PWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS3A5017PWRE4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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#### DGV (R-PDSO-G\*\*)

#### **24 PINS SHOWN**

#### **PLASTIC SMALL-OUTLINE**



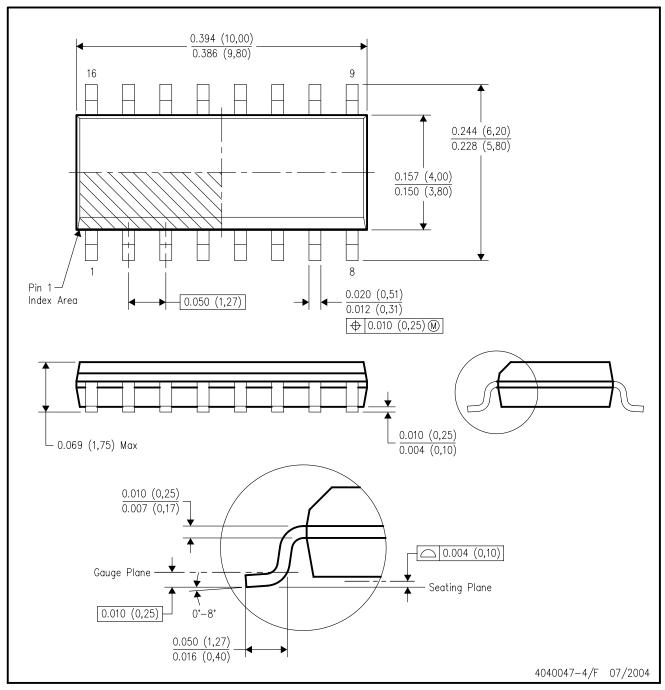
NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
- D. Falls within JEDEC: 24/48 Pins MO-153 14/16/20/56 Pins – MO-194



# D (R-PDSO-G16)

### PLASTIC SMALL-OUTLINE PACKAGE



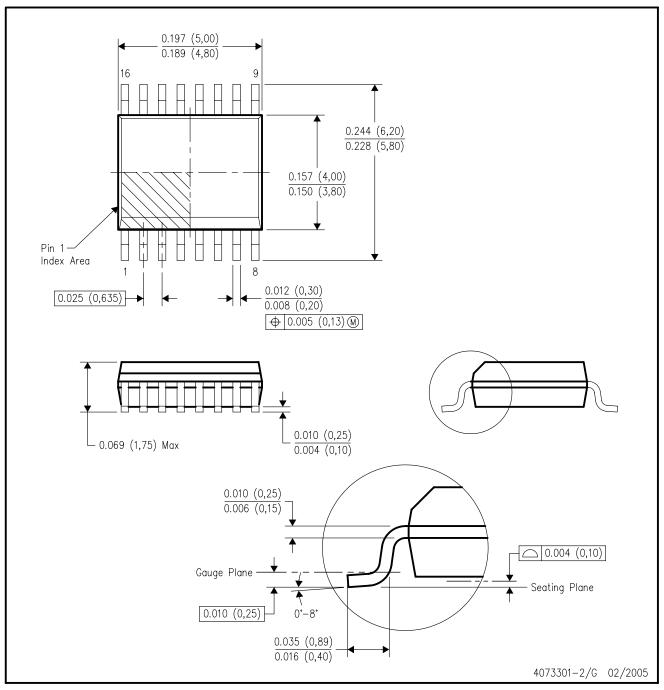
NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-012 variation AC.



## DBQ (R-PDSO-G16)

### PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
- D. Falls within JEDEC MO-137 variation AB.



#### PW (R-PDSO-G\*\*)

#### 14 PINS SHOWN

#### PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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